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Details	
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Speed	-
Connectivity	-
Peripherals	-
Number of I/O	-
Program Memory Size	-
Program Memory Type	-
EEPROM Size	-
RAM Size	-
Voltage - Supply (Vcc/Vdd)	-
Data Converters	-
Oscillator Type	-
Operating Temperature	-
Mounting Type	-
Package / Case	-
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5603bf2cll6

Table 1. MPC5604B/C device comparison[1] (continued)

Feature	Device															
	MPC5602BxLH	MPC5602BxLL	MPC5602BxLQ	MPC5602CxLH	MPC5602CxLL	MPC5603BxLH	MPC5603BxLL	MPC5603BxLQ	MPC5603CxLH	MPC5603CxLL	MPC5604BxLH	MPC5604BxLL	MPC5604BxLQ	MPC5604CxLH	MPC5604CxLL	MPC5604BxMG
• PWM + IC/OC[4]	10 ch	20 ch	40 ch	10 ch	20 ch	10 ch	20 ch	40 ch	10 ch	20 ch	10 ch	20 ch	40 ch	10 ch	20 ch	40 ch
• IC/OC[4]	—	3 ch	6 ch	—	3 ch	—	3 ch	6 ch	—	3 ch	—	3 ch	6 ch	—	3 ch	6 ch
SCI (LINFlex)	3[5]			4												
SPI (DSPI)	2	3		2	3	2	3		2	3	2	3		2	3	
CAN (FlexCAN)	2[6]			5	6	3[7]			5	6	3[7]			5	6	
I^2C	1															
32 kHz oscillator	Yes															
GPIO[8]	45	79	123	45	79	45	79	123	45	79	45	79	123	45	79	123
Debug	JTAG															Nexus2+
Package	64 LQFP	100 LQFP	144 LQFP	64 LQFP	100 LQFP	64 LQFP	100 LQFP	144 LQFP	64 LQFP	100 LQFP	64 LQFP	100 LQFP	144 LQFP	64 LQFP	100 LQFP	208 MAPBGA[9]

1 Feature set dependent on selected peripheral multiplexing—table shows example implementation.

2 Based on 125 °C ambient operating temperature.

3 See the eMIOS section of the device reference manual for information on the channel configuration and functions.

4 IC – Input Capture; OC – Output Compare; PWM – Pulse Width Modulation; MC – Modulus counter.

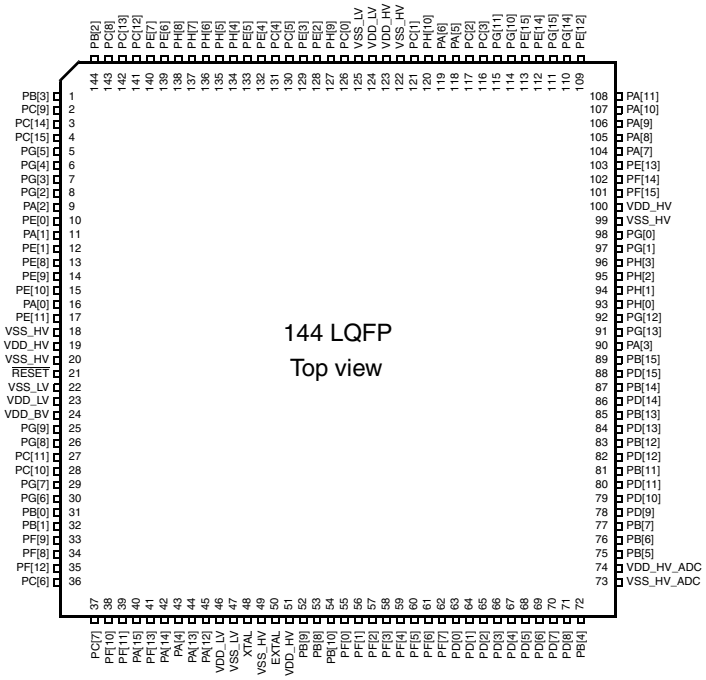
5 SCI0, SCI1 and SCI2 are available. SCI3 is not available.

6 CAN0, CAN1 are available. CAN2, CAN3, CAN4 and CAN5 are not available.

7 CAN0, CAN3 and either CAN1 or CAN4 are available. CAN2, CAN5 and CAN6 are not available

8 I/O count based on multiplexing with peripherals.

9 208 MAPBGA available only as development package for Nexus2+.



Note:
Availability of port pin alternate functions depends on product selection.

Figure 5. LQFP 144-pin configuration

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET configuration	Pin number				
								MPC560xB 64 LQFP	MPC560xC 64 LQFP	100 LQFP	144 LQFP	208 MAPBGA[3]
PC[7]	PCR[39]	AF0 AF1 AF2 AF3 — —	GPIO[39] — — — LIN1RX WKPU[12][4]	SIUL — — — LINFlex_1 WKPU	I/O — — — I I	S	Tristate	17	17	26	37	P3
PC[8]	PCR[40]	AF0 AF1 AF2 AF3	GPIO[40] LIN2TX — —	SIUL LINFlex_2 — —	I/O O — —	S	Tristate	63	63	99	143	A1
PC[9]	PCR[41]	AF0 AF1 AF2 AF3 — —	GPIO[41] — — — LIN2RX WKPU[13][4]	SIUL — — — LINFlex_2 WKPU	I/O — — — I I	S	Tristate	2	2	2	2	B1
PC[10]	PCR[42]	AF0 AF1 AF2 AF3	GPIO[42] CAN1TX CAN4TX[11] MA[1]	SIUL FlexCAN_1 FlexCAN_4 ADC	I/O O O O	M	Tristate	13	13	22	28	M3
PC[11]	PCR[43]	AF0 AF1 AF2 AF3 — — —	GPIO[43] — — — CAN1RX CAN4RX[11] WKPU[5][4]	SIUL — — — FlexCAN_1 FlexCAN_4 WKPU	I/O — — — I I I	S	Tristate	—	—	21	27	M4
PC[12]	PCR[44]	AF0 AF1 AF2 AF3 —	GPIO[44] E0UC[12] — — SIN_2	SIUL eMIOS_0 — — DSPI_2	I/O I/O — — I	M	Tristate	—	—	97	141	B4
PC[13]	PCR[45]	AF0 AF1 AF2 AF3	GPIO[45] E0UC[13] SOUT_2 —	SIUL eMIOS_0 DSPI_2 —	I/O I/O O —	S	Tristate	—	—	98	142	A2
PC[14]	PCR[46]	AF0 AF1 AF2 AF3 —	GPIO[46] E0UC[14] SCK_2 — EIRQ[8]	SIUL eMIOS_0 DSPI_2 — SIUL	I/O I/O I/O — I	S	Tristate	—	—	3	3	C1

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET configuration	Pin number				
								MPC560xB 64 LQFP	MPC560xC 64 LQFP	100 LQFP	144 LQFP	208 MAPBGA[3]
PF[8]	PCR[88]	AF0 AF1 AF2 AF3	GPIO[88] CAN3TX[14] CS4_0 CAN2TX[15]	SIUL FlexCAN_3 DSPI_0 FlexCAN_2	I/O O O O	M	Tristate	—	—	—	34	P1
PF[9]	PCR[89]	AF0 AF1 AF2 AF3 — —	GPIO[89] — CS5_0 — CAN2RX[15] CAN3RX[14]	SIUL — DSPI_0 — FlexCAN_2 FlexCAN_3	I/O — O — I I	S	Tristate	—	—	—	33	N2
PF[10]	PCR[90]	AF0 AF1 AF2 AF3	GPIO[90] — — —	SIUL — — —	I/O — — —	M	Tristate	—	—	—	38	R3
PF[11]	PCR[91]	AF0 AF1 AF2 AF3 —	GPIO[91] — — — WKPU[15][4]	SIUL — — — WKPU	I/O — — — I	S	Tristate	—	—	—	39	R4
PF[12]	PCR[92]	AF0 AF1 AF2 AF3	GPIO[92] E1UC[25] — —	SIUL eMIOS_1 — —	I/O I/O — —	M	Tristate	—	—	—	35	R1
PF[13]	PCR[93]	AF0 AF1 AF2 AF3 —	GPIO[93] E1UC[26] — — WKPU[16][4]	SIUL eMIOS_1 — — WKPU	I/O I/O — — I	S	Tristate	—	—	—	41	T6
PF[14]	PCR[94]	AF0 AF1 AF2 AF3	GPIO[94] CAN4TX[11] E1UC[27] CAN1TX	SIUL FlexCAN_4 eMIOS_1 FlexCAN_4	I/O O I/O O	M	Tristate	—	43	—	102	D14
PF[15]	PCR[95]	AF0 AF1 AF2 AF3 — — —	GPIO[95] — — — CAN1RX CAN4RX[11] EIRQ[13]	SIUL — — — FlexCAN_1 FlexCAN_4 SIUL	I/O — — — I I I	S	Tristate	—	42	—	101	E15

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET configuration	Pin number				
								MPC560xB 64 LQFP	MPC560xC 64 LQFP	100 LQFP	144 LQFP	208 MAPBGA[3]
PH[2]	PCR[114]	AF0 AF1 AF2 AF3	GPIO[114] E1UC[4] SCK_1 —	SIUL eMIOS_1 DSPI_1 —	I/O I/O I/O —	M	Tristate	—	—	—	95	F16
PH[3]	PCR[115]	AF0 AF1 AF2 AF3	GPIO[115] E1UC[5] CS0_1 —	SIUL eMIOS_1 DSPI_1 —	I/O I/O I/O —	M	Tristate	—	—	—	96	F15
PH[4]	PCR[116]	AF0 AF1 AF2 AF3	GPIO[116] E1UC[6] — —	SIUL eMIOS_1 — —	I/O I/O — —	M	Tristate	—	—	—	134	A6
PH[5]	PCR[117]	AF0 AF1 AF2 AF3	GPIO[117] E1UC[7] — —	SIUL eMIOS_1 — —	I/O I/O — —	S	Tristate	—	—	—	135	B6
PH[6]	PCR[118]	AF0 AF1 AF2 AF3	GPIO[118] E1UC[8] — MA[2]	SIUL eMIOS_1 — ADC	I/O I/O — O	M	Tristate	—	—	—	136	D5
PH[7]	PCR[119]	AF0 AF1 AF2 AF3	GPIO[119] E1UC[9] CS3_2 MA[1]	SIUL eMIOS_1 DSPI_2 ADC	I/O I/O O O	M	Tristate	—	—	—	137	C5
PH[8]	PCR[120]	AF0 AF1 AF2 AF3	GPIO[120] E1UC[10] CS2_2 MA[0]	SIUL eMIOS_1 DSPI_2 ADC	I/O I/O O O	M	Tristate	—	—	—	138	A5
PH[9][9]	PCR[121]	AF0 AF1 AF2 AF3	GPIO[121] — TCK —	SIUL — JTAGC —	I/O — I —	S	Input, weak pull-up	60	60	88	127	B8
PH[10][9]	PCR[122]	AF0 AF1 AF2 AF3	GPIO[122] — TMS —	SIUL — JTAGC —	I/O — I —	S	Input, weak pull-up	53	53	81	120	B9

2.8 Electrical characteristics

2.9 Introduction

This section contains electrical characteristics of the device as well as temperature and power considerations.

This product contains devices to protect the inputs against damage due to high static voltages. However, it is advisable to take precautions to avoid applying any voltage higher than the specified maximum rated voltages.

To enhance reliability, unused inputs can be driven to an appropriate logic voltage level (V_{DD} or V_{SS}). This could be done by the internal pull-up and pull-down, which is provided by the product for most general purpose pins.

The parameters listed in the following tables represent the characteristics of the device and its demands on the system.

In the tables where the device logic provides signals with their respective timing characteristics, the symbol “CC” for Controller Characteristics is included in the Symbol column.

In the tables where the external system must provide signals with their respective timing characteristics to the device, the symbol “SR” for System Requirement is included in the Symbol column.

2.10 Parameter classification

The electrical parameters shown in this supplement are guaranteed by various methods. To give the customer a better understanding, the classifications listed in Table 7 are used and the parameters are tagged accordingly in the tables where appropriate.

Table 7. Parameter classifications

Classification tag	Tag description
P	Those parameters are guaranteed during production testing on each individual device.
C	Those parameters are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
T	Those parameters are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters are derived mainly from simulations.

NOTE

The classification is shown in the column labeled “C” in the parameter tables where appropriate.

2.11 NVUSRO register

Bit values in the Non-Volatile User Options (NVUSRO) Register control portions of the device configuration, namely electrical parameters such as high voltage supply and oscillator margin, as well as digital functionality (watchdog enable/disable after reset).

For a detailed description of the NVUSRO register, please refer to the device reference manual.

2.11.1 NVUSRO[PAD3V5V] field description

The DC electrical characteristics are dependent on the PAD3V5V bit value. Table 8 shows how NVUSRO[PAD3V5V] controls the device configuration.

Table 8. PAD3V5V field description

Value[1]	Description
0	High voltage supply is 5.0 V
1	High voltage supply is 3.3 V

[1] Default manufacturing value is ‘1’. Value can be programmed by customer in Shadow Flash.

2.11.2 NVUSRO[OSCILLATOR_MARGIN] field description

The fast external crystal oscillator consumption is dependent on the OSCILLATOR_MARGIN bit value. Table 9 shows how NVUSRO[OSCILLATOR_MARGIN] controls the device configuration.

Table 9. OSCILLATOR_MARGIN field description

Value[1]	Description
0	Low consumption configuration (4 MHz/8 MHz)
1	High margin configuration (4 MHz/16 MHz)

[1] Default manufacturing value is ‘1’. Value can be programmed by customer in Shadow Flash.

2.11.3 NVUSRO[WATCHDOG_EN] field description

The watchdog enable/disable configuration after reset is dependent on the WATCHDOG_EN bit value. Table 10 shows how NVUSRO[WATCHDOG_EN] controls the device configuration.

Table 10. WATCHDOG_EN field description

Value[1]	Description
0	Disable after reset
1	Enable after reset

[1] Default manufacturing value is ‘1’. Value can be programmed by customer in Shadow Flash.

Table 13. Recommended operating conditions (5.0 V)

Symbol		Parameter	Conditions	Value		Unit
				Min	Max	
V_{SS}	SR	Digital ground on VSS_HV pins	—	0	0	V
V_{DD}[1]	SR	Voltage on VDD_HV pins with respect to ground (V_{SS})	—	4.5	5.5	V
			Voltage drop[2]	3.0	5.5	
V_{SS_LV}[3]	SR	Voltage on VSS_LV (low voltage digital supply) pins with respect to ground (V_{SS})	—	V_{SS}–0.1	V_{SS}+0.1	V
V_{DD_BV}[4]	SR	Voltage on VDD_BV pin (regulator supply) with respect to ground (V_{SS})	—	4.5	5.5	V
			Voltage drop[2]	3.0	5.5	
			Relative to V_{DD}	V_{DD}–0.1	V_{DD}+0.1	
V_{SS_ADC}	SR	Voltage on VSS_HV_ADC (ADC reference) pin with respect to ground (V_{SS}	—	V_{SS}–0.1	V_{SS}+0.1	V
V_{DD_ADC}[5]	SR	Voltage on VDD_HV_ADC pin (ADC reference) with respect to ground (V_{SS})	—	4.5	5.5	V
			Voltage drop[2]	3.0	5.5	
			Relative to V_{DD}	V_{DD}–0.1	V_{DD}+0.1	
V_{IN}	SR	Voltage on any GPIO pin with respect to ground (V_{SS})	—	V_{SS}–0.1	—	V
			Relative to V_{DD}	—	V_{DD}+0.1	
I_{INJPAD}	SR	Injected input current on any pin during overload condition	—	–5	5	mA
I_{INJSUM}	SR	Absolute sum of all injected input currents during overload condition	—	–50	50	
TV_{DD}	SR	V_{DD} slope to ensure correct power up[6]	—	3.0[7]	0.25 V/µs	V/s
T_{A} C-Grade Part	SR	Ambient temperature under bias	$f_{CPU} \leq 64$ MHz	–40	85	°C
T_{J} C-Grade Part	SR	Junction temperature under bias		–40	110	
T_{A} V-Grade Part	SR	Ambient temperature under bias		–40	105	
T_{J} V-Grade Part	SR	Junction temperature under bias		–40	130	
T_{A} M-Grade Part	SR	Ambient temperature under bias		–40	125	
T_{J} M-Grade Part	SR	Junction temperature under bias		–40	150	

1 100 nF capacitance needs to be provided between each V_{DD}/V_{SS} pair.

2 Full device operation is guaranteed by design when the voltage drops below 4.5 V down to 3.0 V. However, certain analog electrical characteristics will not be guaranteed to stay within the stated limits.

3 330 nF capacitance needs to be provided between each V_{DD_LV}/V_{SS_LV} supply pair.

4 100 nF capacitance needs to be provided between V_{DD_BV} and the nearest V_{SS_LV} (higher value may be needed depending on external regulator characteristics).

5 1 µF (electrolithic/tantalum) + 47 nF (ceramic) capacitance needs to be provided between V_{DD_ADC}/V_{SS_ADC} pair. Another ceramic cap of 10 nF with low inductance package can be added.

6 Guaranteed by device validation.

7 Minimum value of TV_{DD} must be guaranteed until V_{DD} reaches 2.6 V (maximum value of V_{PORH}).

Table 14. LQFP thermal characteristics[1] (continued)

Symbol		C	Parameter	Conditions[2]	Pin count	Value	Unit
Ψ_{JC}	CC	D	Junction-to-case thermal characterization parameter, natural convection	Single-layer board - 1s	64	TBD	°C/W
					100	9	
					144	10	
				Four-layer board - 2s2p	64	TBD	
					100	9	
					144	10	

1 Thermal characteristics are based on simulation.

2 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C

3 Junction-to-ambient thermal resistance determined per JEDEC JESD51-3 and JESD51-6. Thermal test board meets JEDEC specification for this package.

4 Junction-to-board thermal resistance determined per JEDEC JESD51-8. Thermal test board meets JEDEC specification for the specified package.

5 Junction-to-case at the top of the package determined using MIL-STD 883 Method 1012.1. The cold plate temperature is used for the case temperature. Reported value includes the thermal resistance of the interface layer.

2.14.2 Power considerations

The average chip-junction temperature, T_J, in degrees Celsius, may be calculated using Equation 1:

$$T_J = T_A + (P_D \times R_{\theta JA}) \quad \textit{Eqn. 1}$$

Where:

T_A is the ambient temperature in °C.

$R_{\theta JA}$ is the package junction-to-ambient thermal resistance, in °C/W.

P_D is the sum of P_{INT} and $P_{I/O}$ ($P_D = P_{INT} + P_{I/O}$).

P_{INT} is the product of I_{DD} and V_{DD}, expressed in watts. This is the chip internal power.

$P_{I/O}$ represents the power dissipation on input and output pins; user determined.

Most of the time for the applications, $P_{I/O} < P_{INT}$ and may be neglected. On the other hand, $P_{I/O}$ may be significant, if the device is configured to continuously drive external modules and/or memories.

An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is given by:

$$P_D = K / (T_J + 273\ °C) \quad \textit{Eqn. 2}$$

Therefore, solving equations 1 and 2:

$$K = P_D \times (T_A + 273\ °C) + R_{\theta JA} \times P_D^2 \quad \textit{Eqn. 3}$$

Where:

[1] 208 MAPBGA available only as development package for Nexus2+

Table 22 provides I/O consumption figures.

In order to ensure device reliability, the average current of the I/O on a single segment should remain below the I_{AVGSEG} maximum value.

Table 22. I/O consumption

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
I_{SWTSLW}[2]	CC	D	Dynamic I/O current for SLOW configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	20	mA
					V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	16	
I_{SWTMED}[2]	CC	D	Dynamic I/O current for MEDIUM configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	29	mA
					V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	17	
I_{SWTFST}[2]	CC	D	Dynamic I/O current for FAST configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	110	mA
					V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	50	
I_{RMSSLW}	CC	D	Root mean square I/O current for SLOW configuration	C_L = 25 pF, 2 MHz	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	2.3	mA
				C_L = 25 pF, 4 MHz		—	—	3.2	
				C_L = 100 pF, 2 MHz		—	—	6.6	
				C_L = 25 pF, 2 MHz	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	1.6	
				C_L = 25 pF, 4 MHz		—	—	2.3	
				C_L = 100 pF, 2 MHz		—	—	4.7	
I_{RMSMED}	CC	D	Root mean square I/O current for MEDIUM configuration	C_L = 25 pF, 13 MHz	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	6.6	mA
				C_L = 25 pF, 40 MHz		—	—	13.4	
				C_L = 100 pF, 13 MHz		—	—	18.3	
				C_L = 25 pF, 13 MHz	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	5	
				C_L = 25 pF, 40 MHz		—	—	8.5	
				C_L = 100 pF, 13 MHz		—	—	11	
I_{RMSFST}	CC	D	Root mean square I/O current for FAST configuration	C_L = 25 pF, 40 MHz	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	22	mA
				C_L = 25 pF, 64 MHz		—	—	33	
				C_L = 100 pF, 40 MHz		—	—	56	
				C_L = 25 pF, 40 MHz	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	14	
				C_L = 25 pF, 64 MHz		—	—	20	
				C_L = 100 pF, 40 MHz		—	—	35	

Table 22. I/O consumption (continued)

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
I_{AVGSEG}	SR	D	Sum of all the static I/O current within a supply segment	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	70	mA
				V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	65	

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to125 °C, unless otherwise specified

2 Stated maximum values represent peak consumption that lasts only a few ns during I/O transition.

Table 23 provides the weight of concurrent switching I/Os.

Due to the dynamic current limitations, the sum of the weight of concurrent switching I/Os on a single segment must not exceed 100% to ensure device functionality.

Table 23. I/O weight[1]

Supply segment			Pad	144/100 LQFP				64 LQFP			
				Weight 5 V		Weight 3.3 V		Weight 5 V		Weight 3.3 V	
144 LQFP	100 LQFP	64 LQFP[2]		SRC[3] = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1
4	4	3	PB[3]	10%	—	12%	—	10%	—	12%	—
			PC[9]	10%	—	12%	—	10%	—	12%	—
		—	PC[14]	9%	—	11%	—	—	—	—	—
		—	PC[15]	9%	13%	11%	12%	—	—	—	—
	—	—	PG[5]	9%	—	11%	—	—	—	—	—
	—	—	PG[4]	9%	12%	10%	11%	—	—	—	—
	—	—	PG[3]	9%	—	10%	—	—	—	—	—
4	—	—	PG[2]	8%	12%	10%	10%	—	—	—	—
	4	3	PA[2]	8%	—	9%	—	8%	—	9%	—
		—	PE[0]	8%	—	9%	—	—	—	—	—
		3	PA[1]	7%	—	9%	—	7%	—	9%	—
		—	PE[1]	7%	10%	8%	9%	—	—	—	—
		—	PE[8]	7%	9%	8%	8%	—	—	—	—
		—	PE[9]	6%	—	7%	—	—	—	—	—
		—	PE[10]	6%	—	7%	—	—	—	—	—
		3	PA[0]	5%	8%	6%	7%	5%	8%	6%	7%
		—	PE[11]	5%	—	6%	—	—	—	—	—

Example 2. Simplified regulator

The regulator should be able to provide significant amount of the current during the standby exit process. For example, in case of an ideal voltage regulator providing 200 mA current, it is possible to recalculate the equivalent ESR_{STDBY}(MAX) and C_{STDBY}(MIN) as follows:

$$ESR_{STDBY}(MAX) = |\Delta_{VDD(STDBY)}|/(I_{DD\_BV} - 200\ mA) = (30\ mV)/(100\ mA) = 0.3\ \Omega$$

$$C_{STDBY}(MIN) = (I_{DD\_BV} - 200\ mA)/dVDD(STDBY)/dt = (300\ mA - 200\ mA)/(15\ mV/\mu s) = 6.7\ \mu F$$

In case optimization is required, C_{STDBY}(MIN) and ESR_{STDBY}(MAX) should be calculated based on the regulator characteristics as well as the board V_{DD} plane characteristics.

2.17.2 Low voltage detector electrical characteristics

The device implements a Power-on Reset (POR) module to ensure correct power-up initialization, as well as four low voltage detectors (LVDs) to monitor the V_{DD} and the V_{DD_LV} voltage while device is supplied:

- POR monitors V_{DD} during the power-up phase to ensure device is maintained in a safe reset state (refer to RGM Destructive Event Status (RGM_DES) Register flag F_POR in device reference manual)
- LVDHV3 monitors V_{DD} to ensure device reset below minimum functional supply (refer to RGM Destructive Event Status (RGM_DES) Register flag F_LVD27 in device reference manual)
- LVDHV5 monitors V_{DD} when application uses device in the 5.0 V ± 10% range (refer to RGM Functional Event Status (RGM_FES) Register flag F_LVD45 in device reference manual)
- LVDLVCOR monitors power domain No. 1 (refer to RGM Destructive Event Status (RGM_DES) Register flag F_LVD12_PD1 in device reference manual
- LVDLVBKP monitors power domain No. 0 (refer to RGM Destructive Event Status (RGM_DES) Register flag F_LVD12_PD0 in device reference manual)

NOTE

When enabled, power domain No. 2 is monitored through LVDLVBKP.

Table 29. Flash module life

Symbol		C	Parameter	Conditions	Value			Unit
					Min	Typ	Max	
P/E	CC	C	Number of program/erase cycles per block over the operating temperature range (T_J)	16 KB blocks	100,000	—	—	cycles
				32 KB blocks	10,000	100,000	—	
				128 KB blocks	1,000	100,000	—	
Retention	CC	C	Minimum data retention at 85 °C average ambient temperature[1]	Blocks with 0–1,000 P/E cycles	20	—	—	years
				Blocks with 1,001–10,000 P/E cycles	10	—	—	
				Blocks with 10,001–100,000 P/E cycles	5	—	—	

1 Ambient temperature averaged over duration of application, not to exceed recommended product operating temperature range.

ECC circuitry provides correction of single bit faults and is used to improve further automotive reliability results. Some units will experience single bit corrections throughout the life of the product with no impact to product reliability.

Table 30. Flash read access timing

Symbol		C	Parameter	Conditions[1]	Max	Unit
f_{READ}	CC	P	Maximum frequency for Flash reading	2 wait states	64	MHz
		C		1 wait state	40	
		C		0 wait states	20	

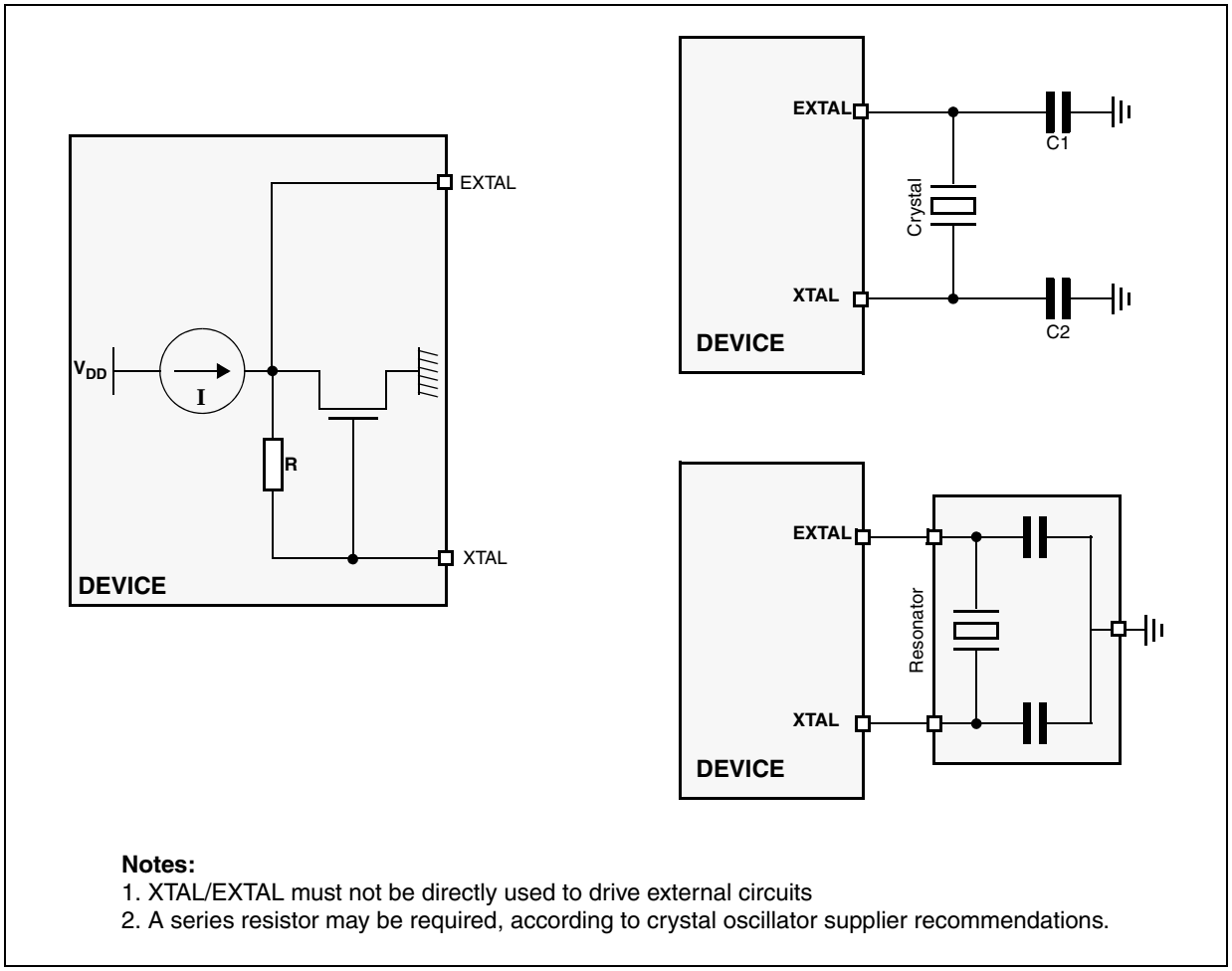
1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

2.19.2 Flash power supply DC characteristics

Table 31 shows the power supply DC characteristics on external supply.

Table 31. Flash memory power supply DC electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
I_{FREAD}[2]	CC	D	Sum of the current consumption on VDD_HV and VDD_BV on read access	Code flash memory module read f_{CPU} = 64 MHz[3]	—	15	33	mA
				Data flash memory module read f_{CPU} = 64 MHz[3]	—	15	33	



Notes:
1. XTAL/EXTAL must not be directly used to drive external circuits
2. A series resistor may be required, according to crystal oscillator supplier recommendations.

Figure 14. Crystal oscillator and resonator connection scheme

Table 36. Crystal description

Nominal frequency (MHz)	NDK crystal reference	Crystal equivalent series resistance ESR Ω	Crystal motional capacitance (C_m) fF	Crystal motional inductance (L_m) mH	Load on xtalin/xtalout C1 = C2 (pF)[1]	Shunt capacitance between xtalout and xtalin C0[2] (pF)
4	NX8045GB	300	2.68	591.0	21	2.93
8	NX5032GA	300	2.46	160.7	17	3.01
10		150	2.93	86.6	15	2.91
12		120	3.11	56.5	15	2.93
16		120	3.90	25.3	10	3.00

1 The values specified for C1 and C2 are the same as used in simulations. It should be ensured that the testing includes all the parasitics (from the board, probe, crystal, etc.) as the AC / transient behavior depends upon them.

2 The value of C0 specified here includes 2 pF additional capacitance for parasitics (to be seen with bond-pads, package, etc.).

2 This is the recommended range of load capacitance at OSC32K_XTAL and OSC32K_EXTAL with respect to ground. It includes all the parasitics due to board traces, crystal and package.

3 Maximum ESR (R_m) of the crystal is 50 kΩ

4 C0 includes a parasitic capacitance of 2.0 pF between OSC32K_XTAL and OSC32K_EXTAL pins

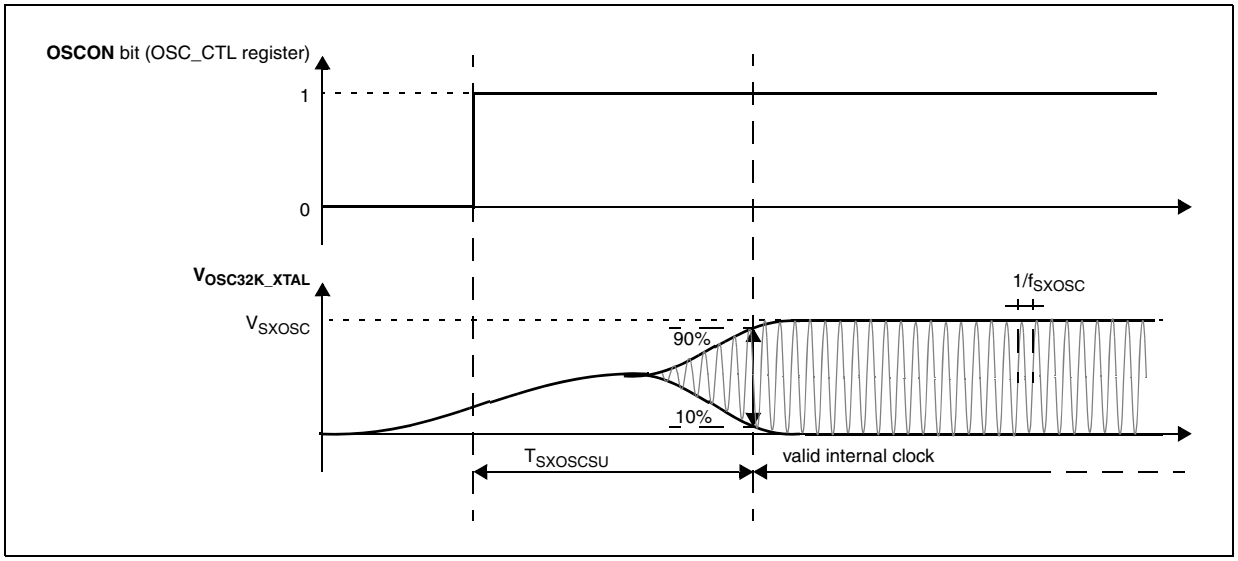


Figure 18. Slow external crystal oscillator (32 kHz) timing diagram

Table 39. Slow external crystal oscillator (32 kHz) electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
f_{SXOSC}	SR	—	Slow external crystal oscillator frequency	—	32	32.768	40	kHz
V_{SXOSC}	CC	T	Oscillation amplitude	—	—	2.1	—	V
$I_{SXOSCBIAS}$	CC	T	Oscillation bias current	—	—	2.5	—	µA
I_{SXOSC}	CC	T	Slow external crystal oscillator consumption	—	—	—	8	µA
$T_{SXOSCSU}$	CC	T	Slow external crystal oscillator start-up time	—	—	—	2^2	s

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified. Values are specified for no neighbor GPIO pin activity. If oscillator is enabled (OSC32K_XTAL and OSC32K_EXTAL pins), neighboring pins should not toggle.

2 Start-up time has been measured with EPSON TOYOCOM MC306 crystal. Variation may be seen with other crystal.

2.23 FMPLL electrical characteristics

The device provides a frequency-modulated phase-locked loop (FMPLL) module to generate a fast system clock from the main oscillator driver.

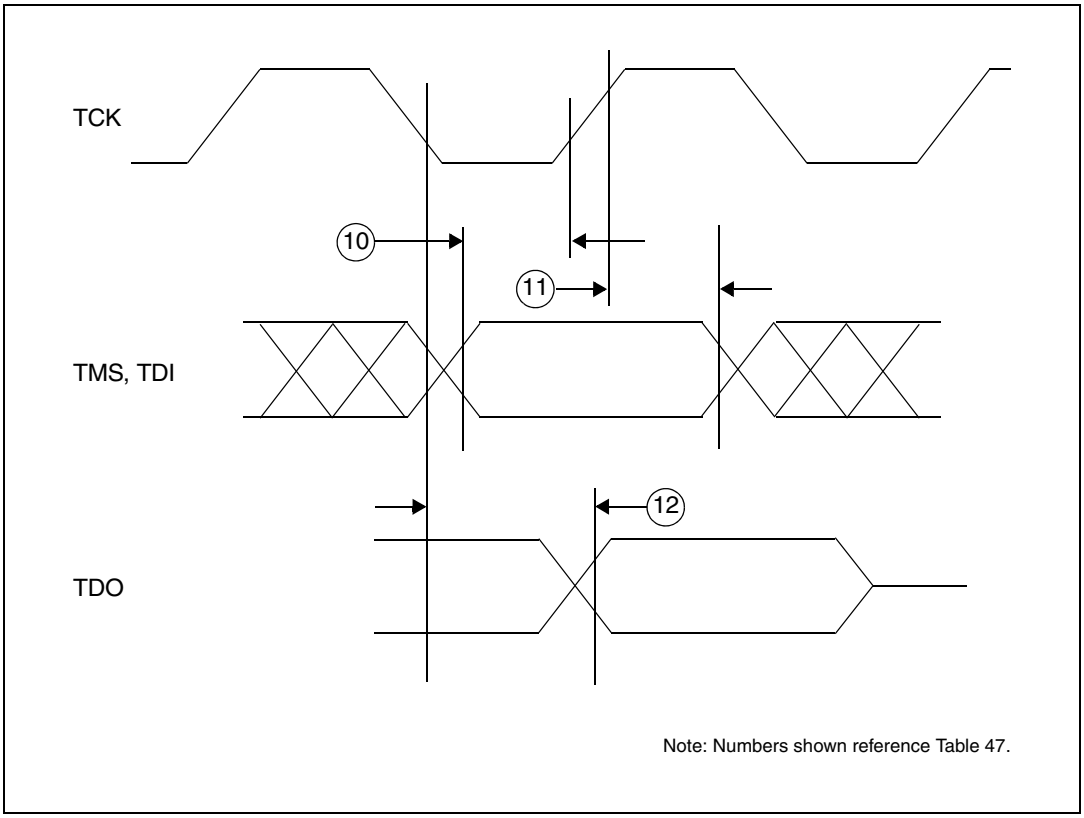


Figure 33. Nexus TDI, TMS, TDO timing

2.27.4 JTAG characteristics

Table 48. JTAG characteristics

No.	Symbol		C	Parameter	Value			Unit
					Min	Typ	Max	
1	t_{JCYC}	CC	D	TCK cycle time	64	—	—	ns
2	t_{TDIS}	CC	D	TDI setup time	15	—	—	ns
3	t_{TDIH}	CC	D	TDI hold time	5	—	—	ns
4	t_{TMSS}	CC	D	TMS setup time	15	—	—	ns
5	t_{TMSH}	CC	D	TMS hold time	5	—	—	ns
6	t_{TDOV}	CC	D	TCK low to TDO valid	—	—	33	ns
7	t_{TDOI}	CC	D	TCK low to TDO invalid	6	—	—	ns

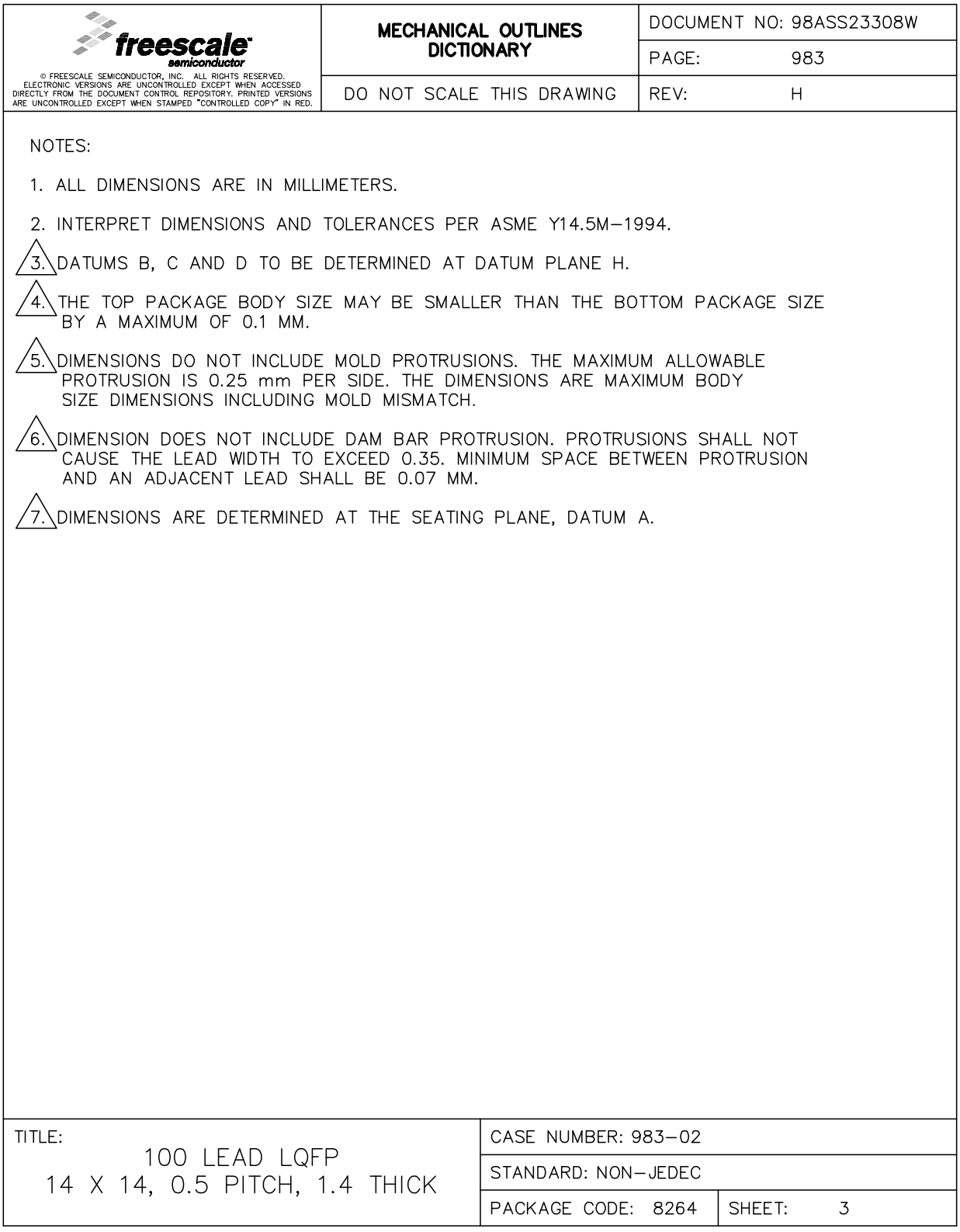


Figure 40. 100 LQFP package mechanical drawing (3 of 3)

3.1.3 144 LQFP

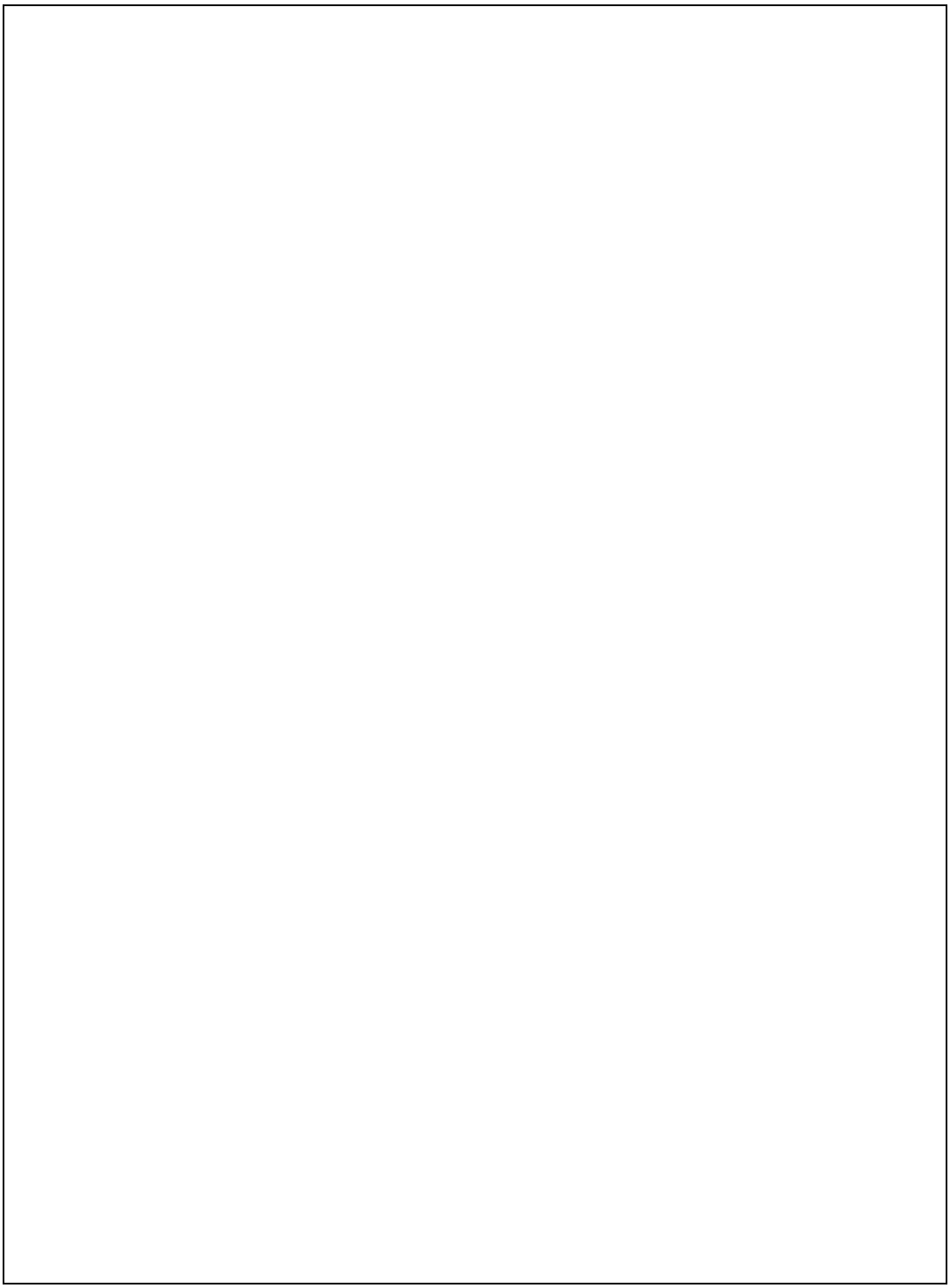


Figure 41. 144 LQFP package mechanical drawing (1 of 2)

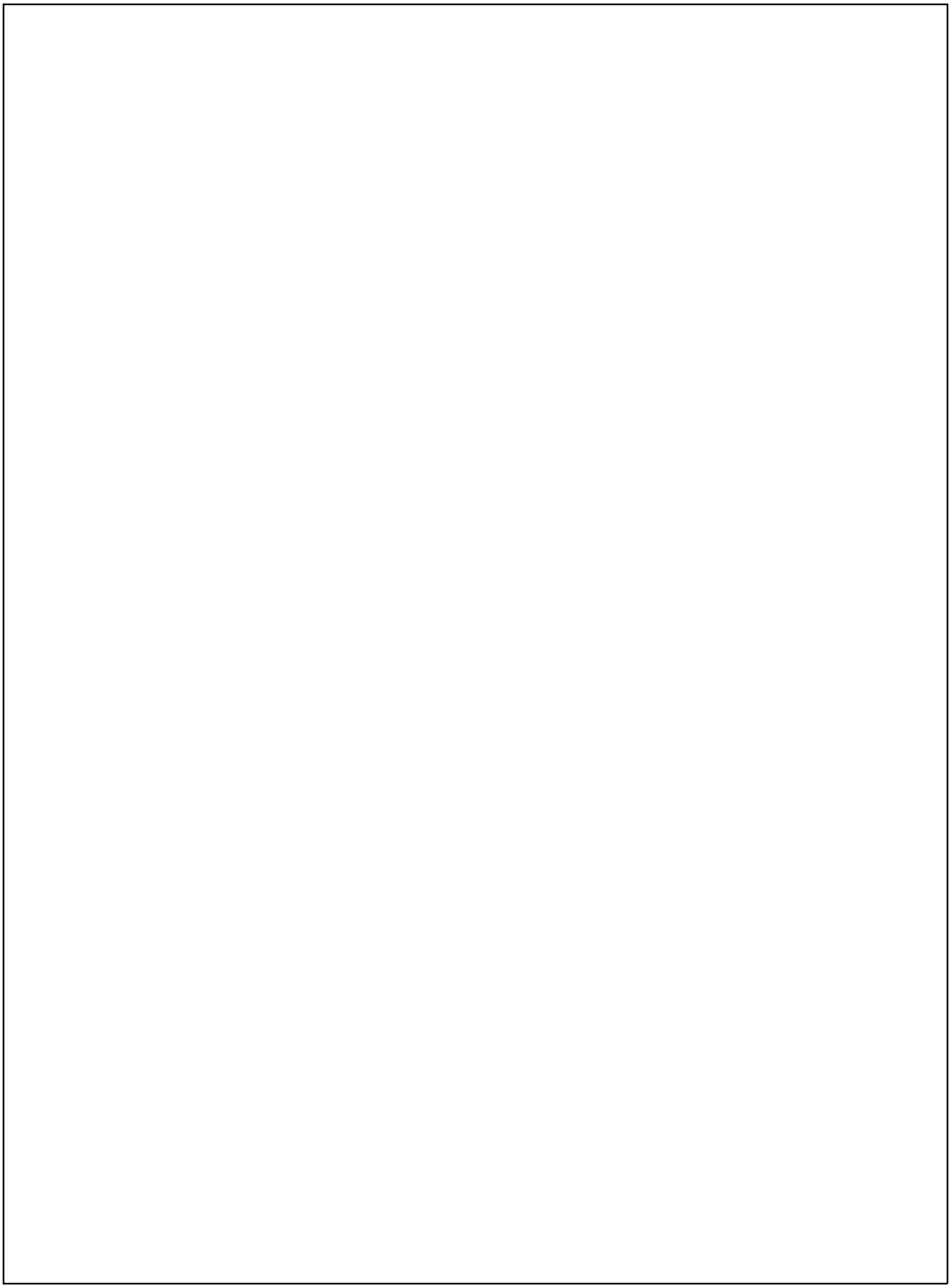


Figure 42. 144 LQFP package mechanical drawing (2 of 2)

Table 49. Revision history (continued)

Revision	Date	Description of Changes
9	16 June 2011	Formatting and minor editorial changes throughout Harmonized oscillator nomenclature Removed all instances of note “All 64 LQFP information is indicative and must be confirmed during silicon validation.” Device comparison table: changed temperature value in footnote 2 from 105 °C to 125 °C MPC560xB LQFP 64-pin configuration and MPC560xC LQFP 64-pin configuration: renamed pin 6 from VPP_TEST to VSS_HV Removed “Pin Muxing” section; added sections “Pad configuration during reset phases”, “Voltage supply pins”, “Pad types”, “System pins,” “Functional ports”, and “Nexus 2+ pins” Section “NVUSRO register”: edited content to separate configuration into electrical parameters and digital functionality; updated footnote describing default value of ‘1’ in field descriptions NVUSRO[PAD3V5V] and NVUSRO[OSCILLATOR_MARGIN] Added section “NVUSRO[WATCHDOG_EN] field description” Recommended operating conditions (3.3 V) and Recommended operating conditions (5.0 V): updated conditions for ambient and junction temperature characteristics I/O input DC electrical characteristics: updated I_{LKG} characteristics Section “I/O pad current specification”: removed content referencing the I_{DYNSEG} maximum value I/O consumption: replaced instances of “Root medium square” with “Root mean square” I/O weight: replaced instances of bit “SRE” with “SRC”; added pads PH[9] and PH[10]; added supply segments; removed weight values in 64-pin LQFP for pads that do not exist in that package Reset electrical characteristics: updated parameter classification for $\|I_{WPU}\|$ Updated Voltage regulator electrical characteristics Section “Low voltage detector electrical characteristics”: changed title (was “Voltage monitor electrical characteristics”); added event status flag names found in RGM chapter of device reference manual to POR module and LVD descriptions; replaced instances of “Low voltage monitor” with “Low voltage detector”; updated values for $V_{LVDLVBKPL}$ and $V_{LVDLVCORL}$; replaced “LVD_DIGBKP” with “LVDLVBKP” in note Updated section “Power consumption” Fast external crystal oscillator (4 to 16 MHz) electrical characteristics: updated parameter classification for $V_{FXOSCOP}$ Crystal oscillator and resonator connection scheme: added footnote about possibility of adding a series resistor Slow external crystal oscillator (32 kHz) electrical characteristics: updated footnote 1 FMPLL electrical characteristics: added short term jitter characteristics; inserted “—” in empty min value cell of t_{lock} row Section “Input impedance and ADC accuracy”: changed “V_A/V_{A2}” to “V_{A2}/V_A” in Equation 11 ADC input leakage current: updated I_{LKG} characteristics ADC conversion characteristics: updated symbols On-chip peripherals current consumption: changed “supply current on “$V_{DD\_HV\_ADC}$” to “supply current on” V_{DD_HV}” in $I_{DD\_HV(FLASH)}$ row; updated $I_{DD\_HV(PLL)}$ value—was 3 * f_{periph}, is 30 * f_{periph}; updated footnotes DSPI characteristics: added rows t_{PCSC} and t_{PASC} Added DSPI PCS strobe (PCSS) timing diagram